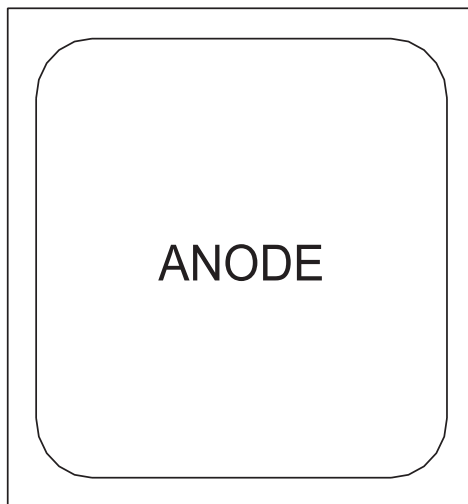


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	98 x 98 MILS
Die Thickness	10.4 MILS
Anode Bonding Pad Area	82.5 x 82.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER

1,170

PRINCIPAL DEVICE TYPES

CR6A2GPP Series

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centrasemi.com/chip

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R1 (1-August 2002)